

TRENCHSTOP™ 5 Advanced Isolation

High speed 5 IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

Features and Benefits:

TRENCHSTOP™ 5 technology offering

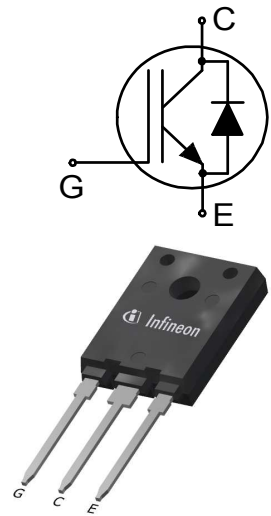
- Best-in-Class efficiency in hard switching and resonant topologies
- Plug and play replacement of previous generation IGBTs
- 650V breakdown voltage
- Low gate charge Q_G
- Very soft, fast recovery antiparallel diode
- Maximum junction temperature 175°C
- 2500V_{RMS} electrical isolation, 50/60Hz, $t=1\text{min}$
- 100% tested isolated mounting surface
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Potential Applications:

- Residential and Commercial Aircon PFC
- Welding converters
- Mid to high range switching frequency converters

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Fully isolated package TO-247

**Key Performance and Package Parameters**

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IKFW75N65EH5	650V	60A	1.65V	175°C	K75EEH5	PG-HSIP247-3-2



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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_h = 25^{\circ}\text{C}$ value limited by bondwire $T_h = 65^{\circ}\text{C}$ $T_h = 65^{\circ}\text{C}$	I_C	80.0 66.0 104.0 ¹⁾	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	240.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	240.0	A
Diode forward current, limited by T_{vjmax} $T_h = 25^{\circ}\text{C}$ value limited by bondwire $T_h = 65^{\circ}\text{C}$	I_F	80.0 74.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	240.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_h = 25^{\circ}\text{C}$ Power dissipation $T_h = 65^{\circ}\text{C}$	P_{tot}	148.0 109.0	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm
Isolation voltage RMS, $f = 50/60\text{Hz}$, $t = 1\text{min}^{2)}$	V_{isol}	2500	V

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, ³⁾ junction - heatsink	R _{th(j-h)}		-	0.86	1.01	K/W
Diode thermal resistance, ³⁾ junction - heatsink	R _{th(j-h)}		-	0.97	1.14	K/W
Thermal resistance junction - ambient	R _{th(j-a)}		-	-	65	K/W

¹⁾ Equivalent current rating in TO-247-3 at $T_h = 65^{\circ}\text{C}$ using reference insulation material: 152 μm , 0.9 W/mK, standard polyimide based reinforced carrier insulator

²⁾ For a proper handling and assembly of the advanced isolation device in the application refer to the note at the package drawing.

³⁾ At force on body $F = 500\text{N}$, $T_a = 25^{\circ}\text{C}$

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.50mA$	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 60.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.65 1.95	2.10 -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 60.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.45 1.39	1.70 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.60mA, V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- -	40 2000	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 60.0A$	-	72.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V f = 1000kHz	-	3600	-	pF
Output capacitance	C _{oes}		-	105	-	
Reverse transfer capacitance	C _{res}		-	13	-	
Gate charge	Q _G	V _{CC} = 520V, I _C = 60.0A, V _{GE} = 15V	-	144.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L _E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 60.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(\text{on})} = 12.0\Omega, R_{G(\text{off})} = 12.0\Omega,$ $L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	30	-	ns
Rise time	t_r		-	35	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	206	-	ns
Fall time	t_f		-	42	-	ns
Turn-on energy	E_{on}		-	1.80	-	mJ
Turn-off energy	E_{off}		-	0.60	-	mJ
Total switching energy	E_{ts}		-	2.40	-	mJ

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Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 60.0\text{A},$ $di_F/dt = 1000\text{A}/\mu\text{s}$	-	75	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.40	-	μC
Diode peak reverse recovery current	I_{rrm}		-	23.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1150	-	$\text{A}/\mu\text{s}$

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 60.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega,$ $L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	29	-	ns
Rise time	t_r		-	36	-	ns
Turn-off delay time	$t_{d(off)}$		-	228	-	ns
Fall time	t_f		-	36	-	ns
Turn-on energy	E_{on}		-	2.40	-	mJ
Turn-off energy	E_{off}		-	0.72	-	mJ
Total switching energy	E_{ts}		-	3.12	-	mJ

Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 60.0\text{A},$ $di_F/dt = 1000\text{A}/\mu\text{s}$	-	118	-	ns
Diode reverse recovery charge	Q_{rr}		-	3.40	-	μC
Diode peak reverse recovery current	I_{rrm}		-	36.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1700	-	$\text{A}/\mu\text{s}$

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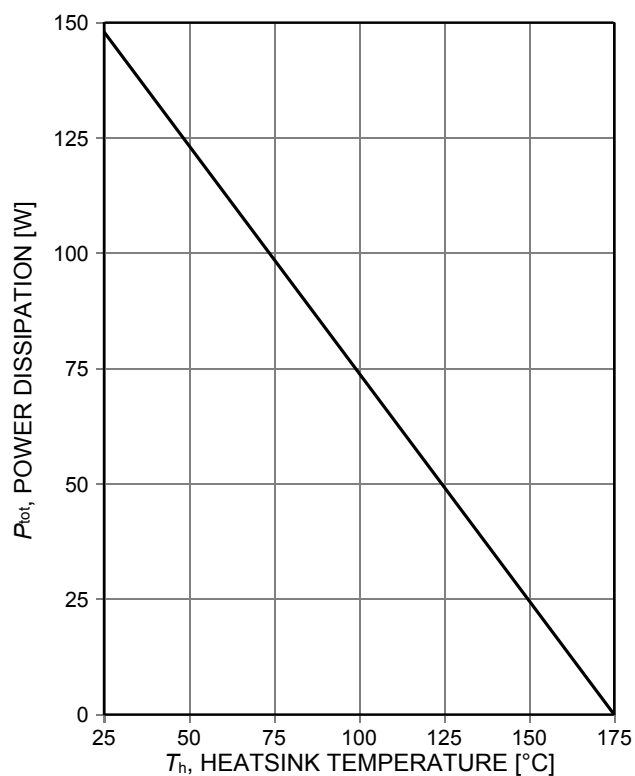


Figure 1. **Power dissipation as a function of heatsink temperature**
($T_j \leq 175^\circ\text{C}$)

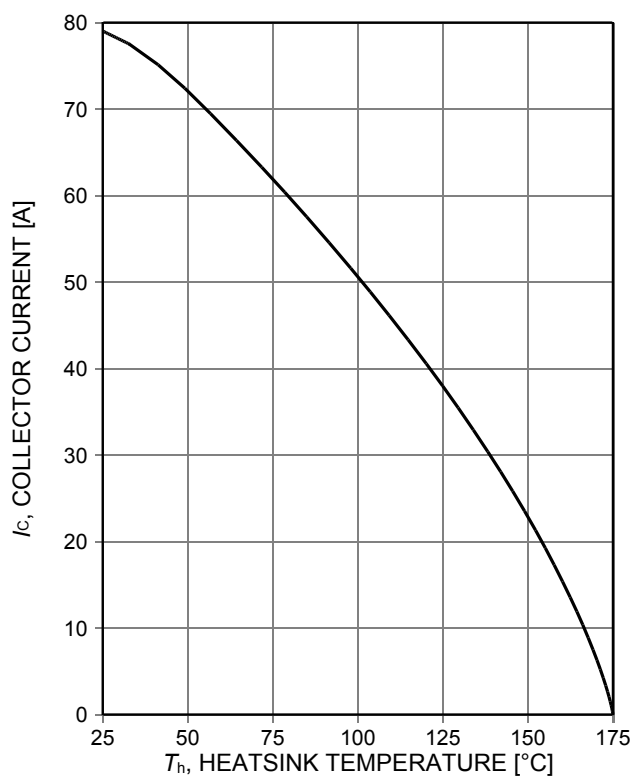


Figure 2. **Collector current as a function of heatsink temperature**
($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

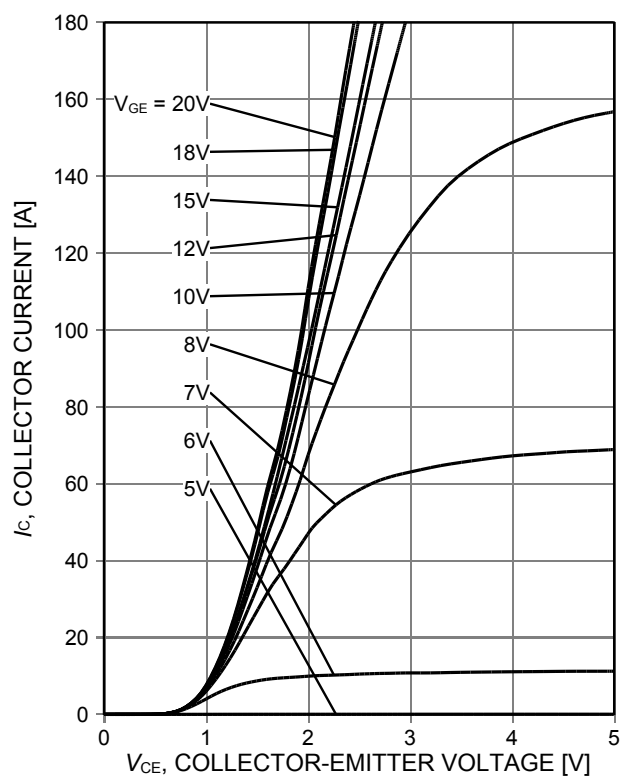


Figure 3. **Typical output characteristic**
($T_j = 25^\circ\text{C}$)

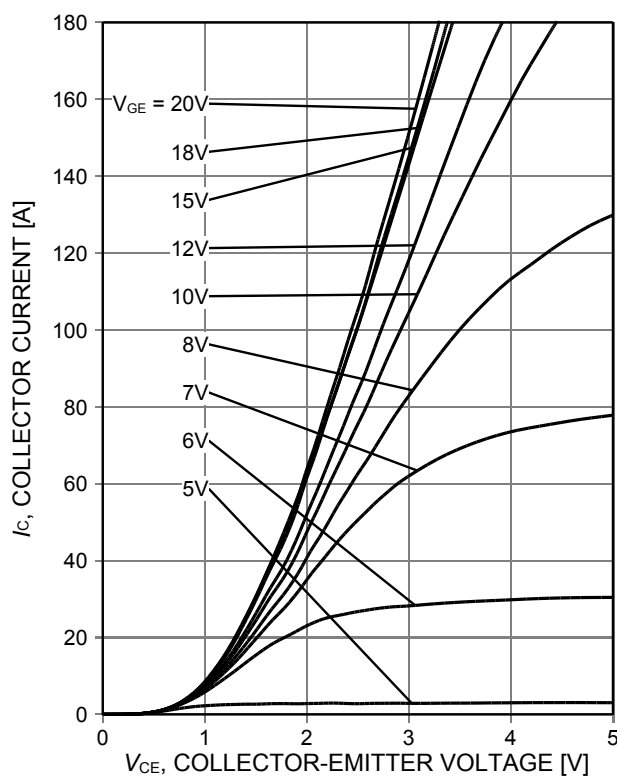


Figure 4. **Typical output characteristic**
($T_j = 175^\circ\text{C}$)

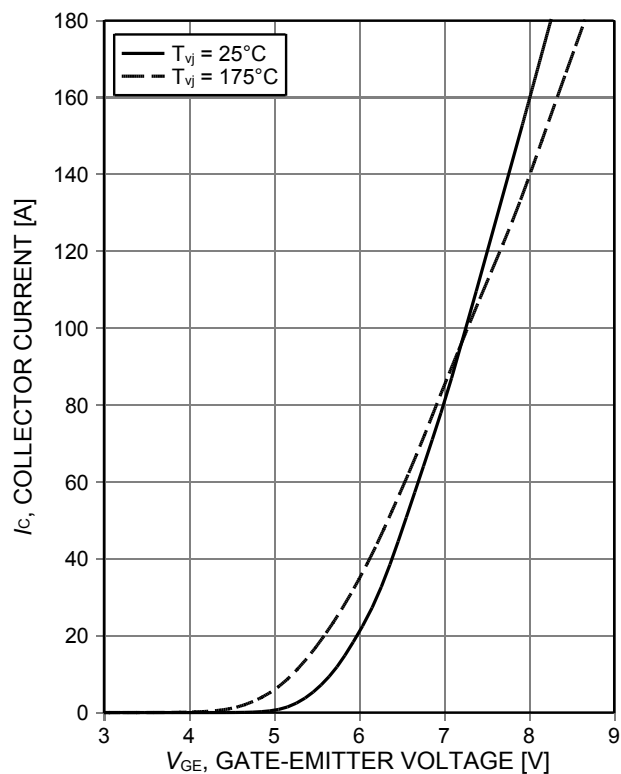


Figure 5. **Typical transfer characteristic**
($V_{CE}=20V$)

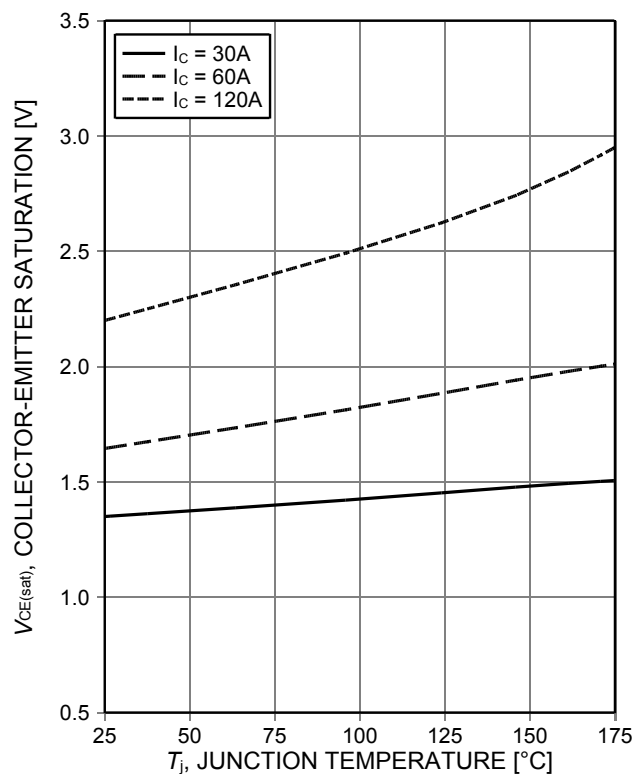


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15V$)

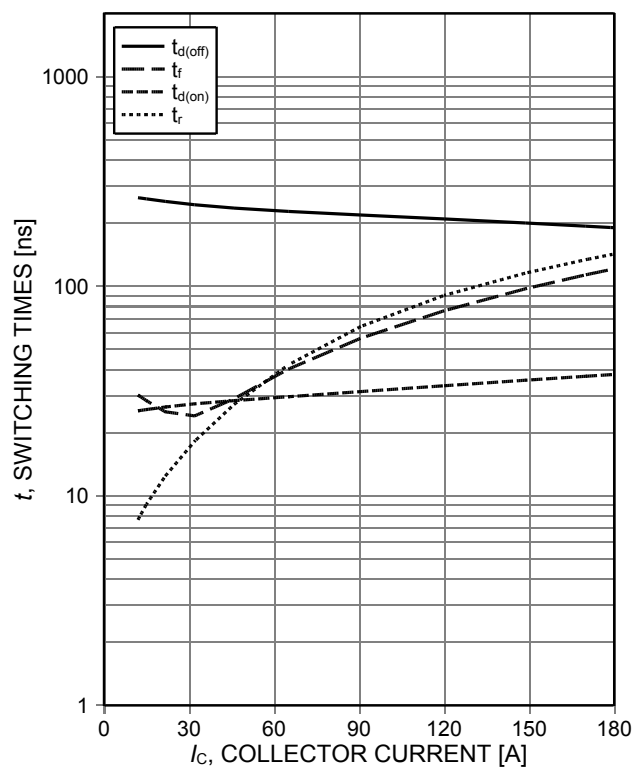


Figure 7. **Typical switching times as a function of collector current**
(ind. load, $T_j=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $R_G=12\Omega$, test circuit in Fig. E)

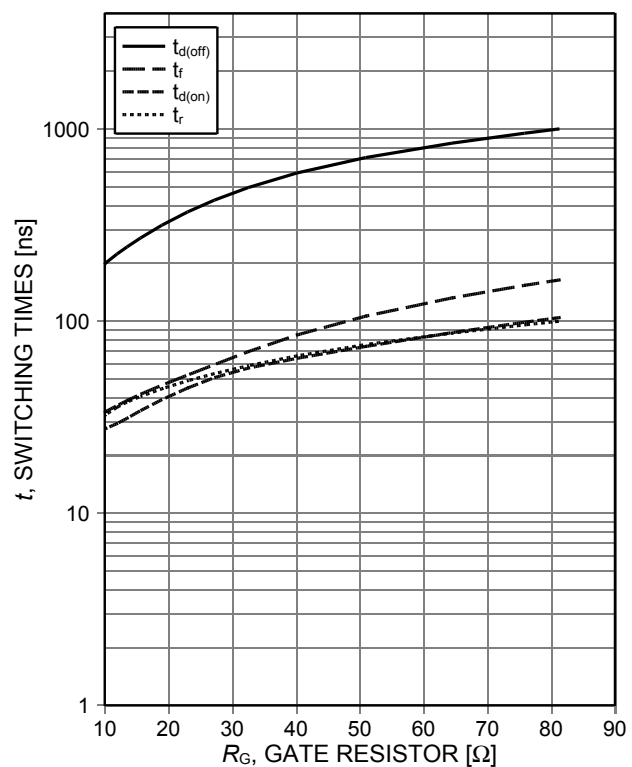


Figure 8. **Typical switching times as a function of gate resistor**
(ind. load, $T_j=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=60A$, test circuit in Fig. E)

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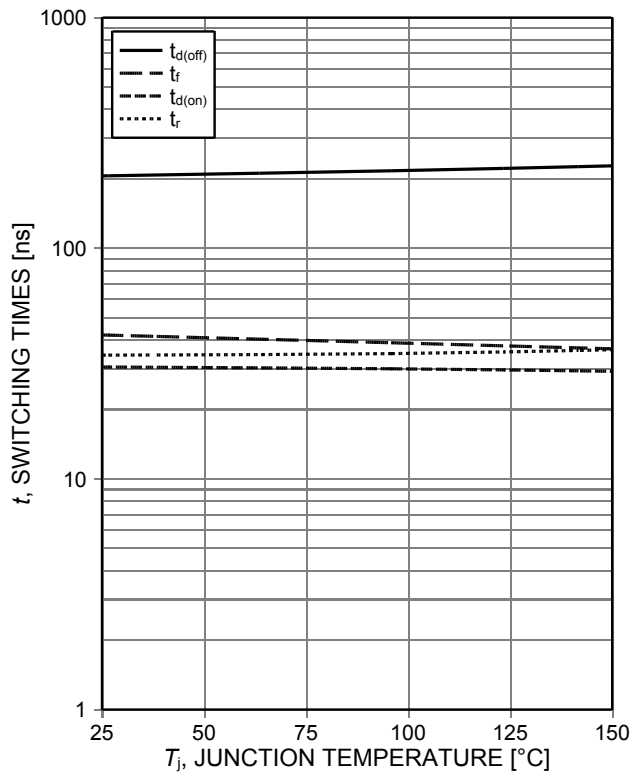


Figure 9. **Typical switching times as a function of junction temperature**
(ind. load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=60A$, $r_G=12\Omega$, test circuit in Fig. E)

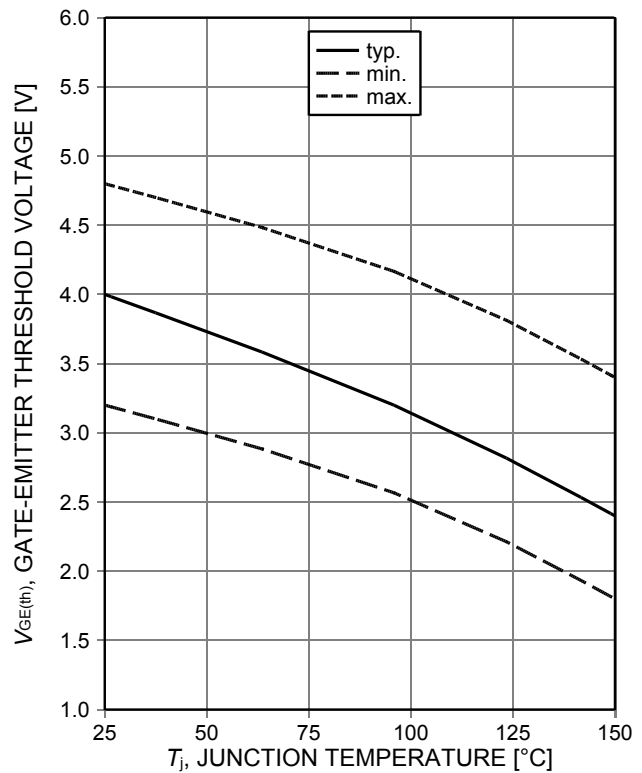


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0.6mA$)

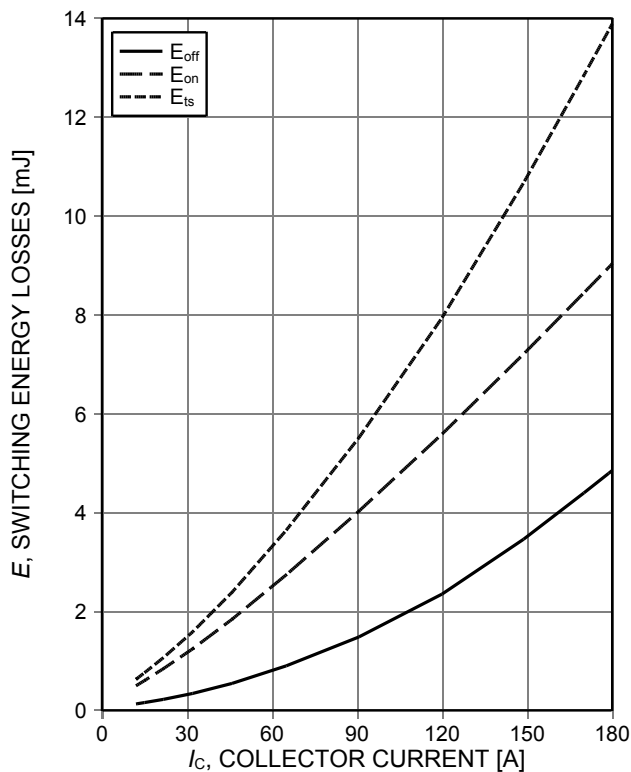


Figure 11. **Typical switching energy losses as a function of collector current**
(ind. load, $T_J=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $R_G=12\Omega$, test circuit in Fig. E)

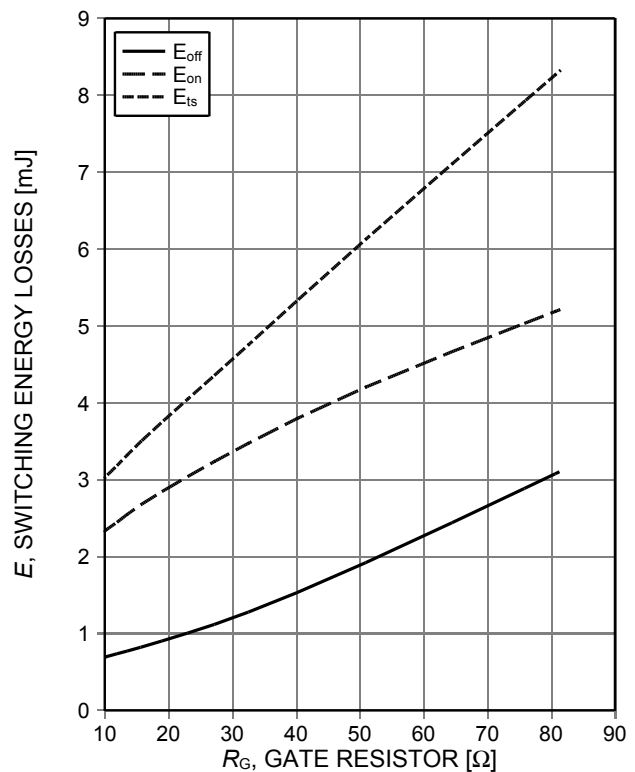


Figure 12. **Typical switching energy losses as a function of gate resistor**
(ind. load, $T_J=150^\circ C$, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=60A$, test circuit in Fig. E)

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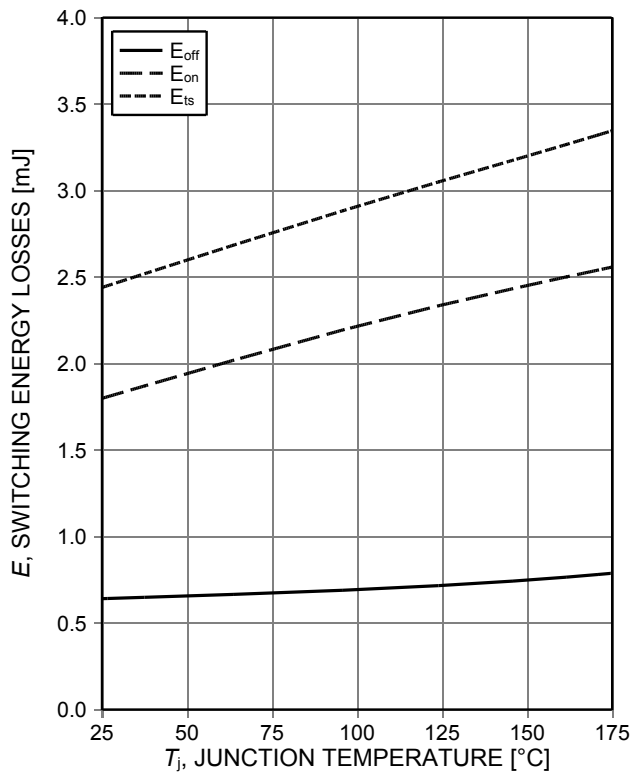


Figure 13. **Typical switching energy losses as a function of junction temperature**
(ind. load, $V_{CE}=400V$, $V_{GE}=0/15V$, $I_C=60A$, $R_G=12\Omega$, test circuit in Fig. E)

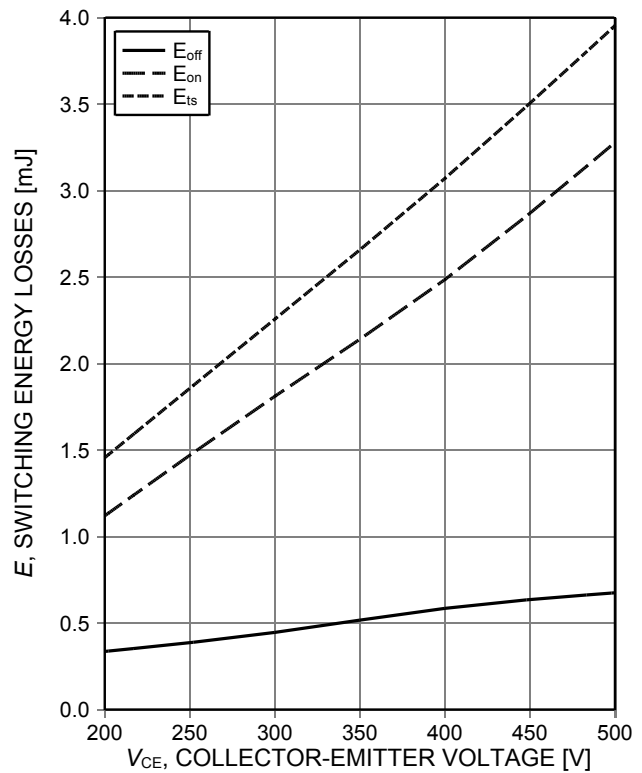


Figure 14. **Typical switching energy losses as a function of collector emitter voltage**
(ind. load, $T_j=150^\circ C$, $V_{GE}=0/15V$, $I_C=60A$, $R_G=12\Omega$, test circuit in Fig. E)

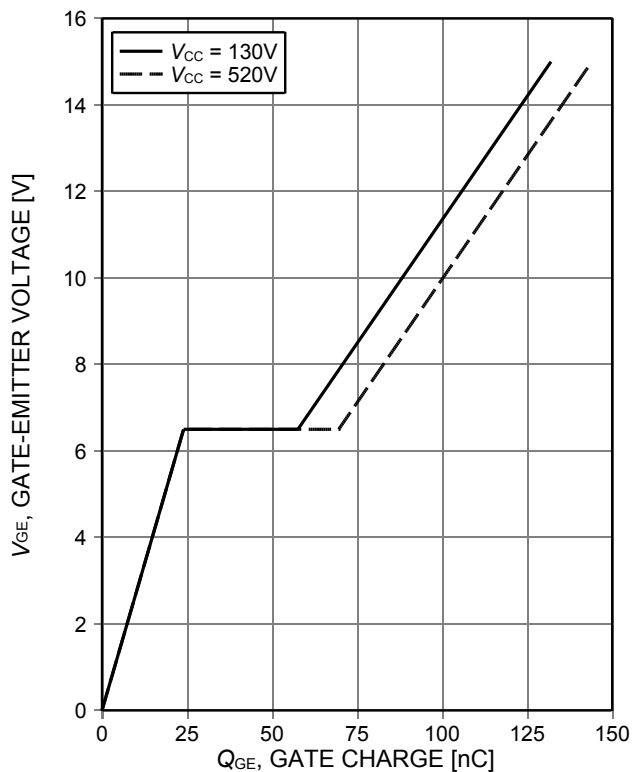


Figure 15. **Typical gate charge**
($I_C=60A$)

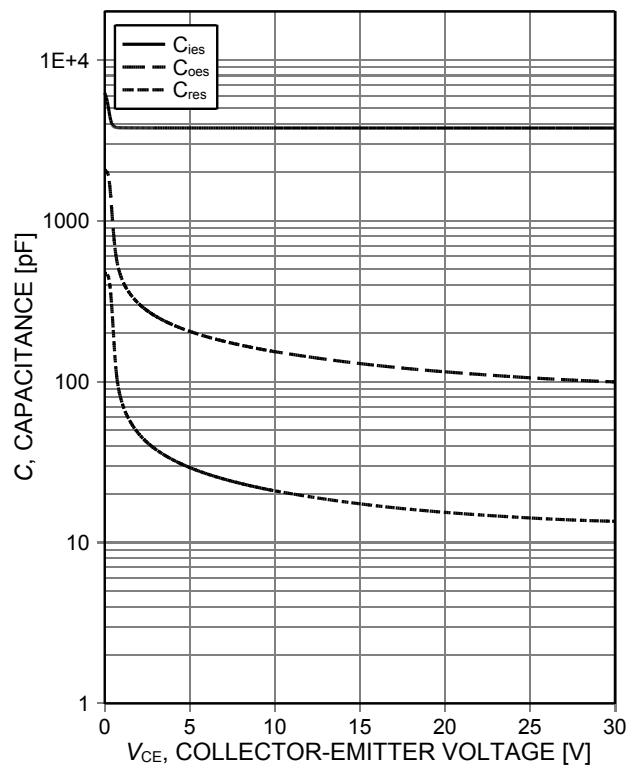


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

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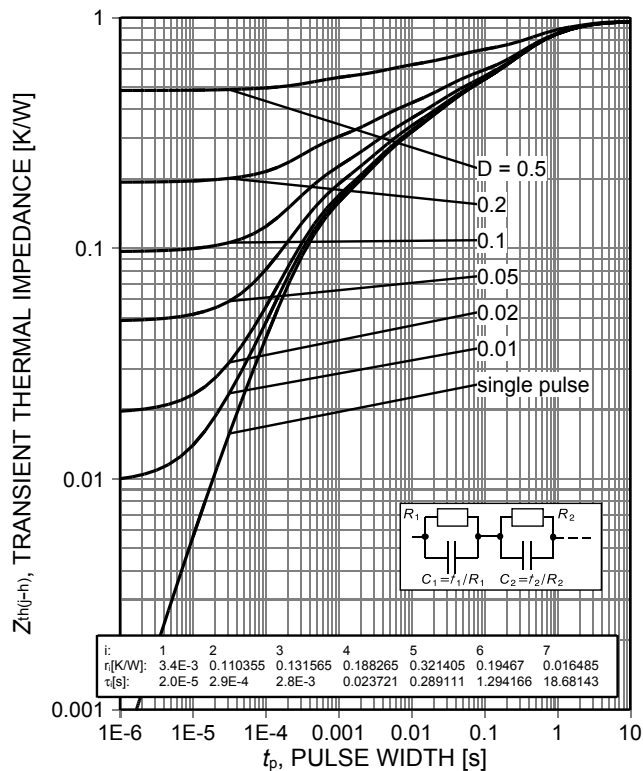


Figure 17. IGBT transient thermal impedance as a function of pulse width
($D=t_p/T$)

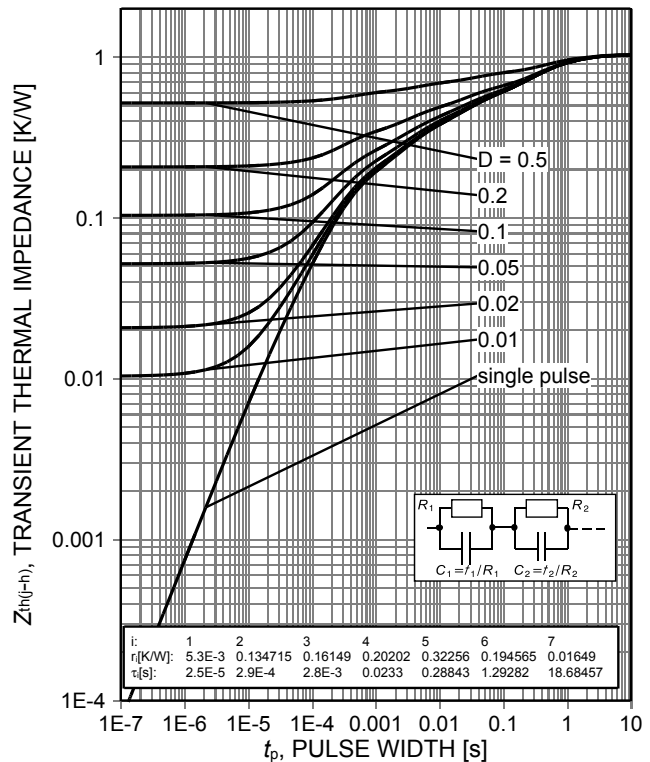


Figure 18. Diode transient thermal impedance as a function of pulse width
($D=t_p/T$)

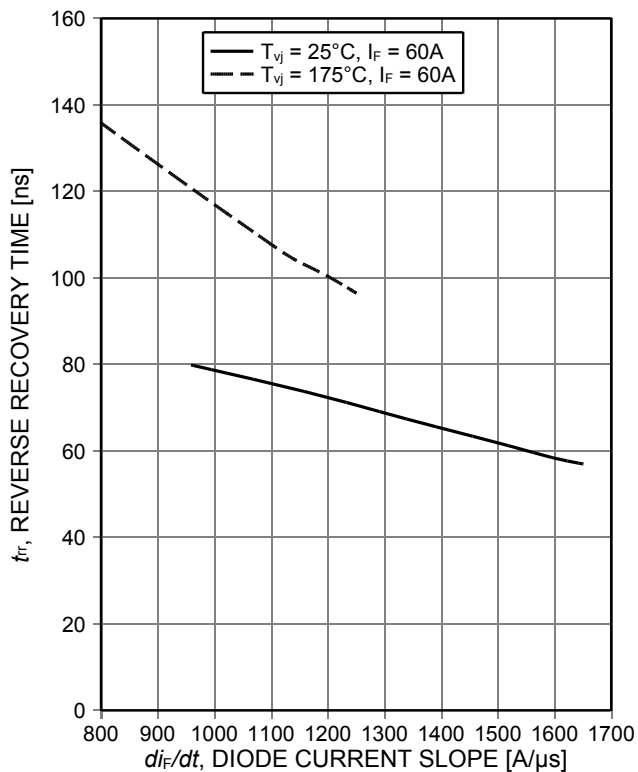


Figure 19. Typical reverse recovery time as a function of diode current slope
($V_R=400V$)

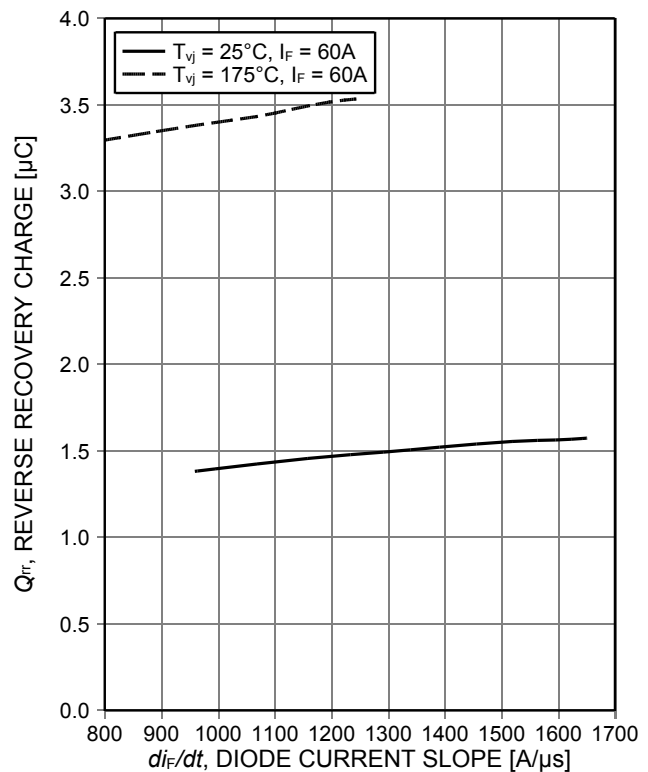


Figure 20. Typical reverse recovery charge as a function of diode current slope
($V_R=400V$)

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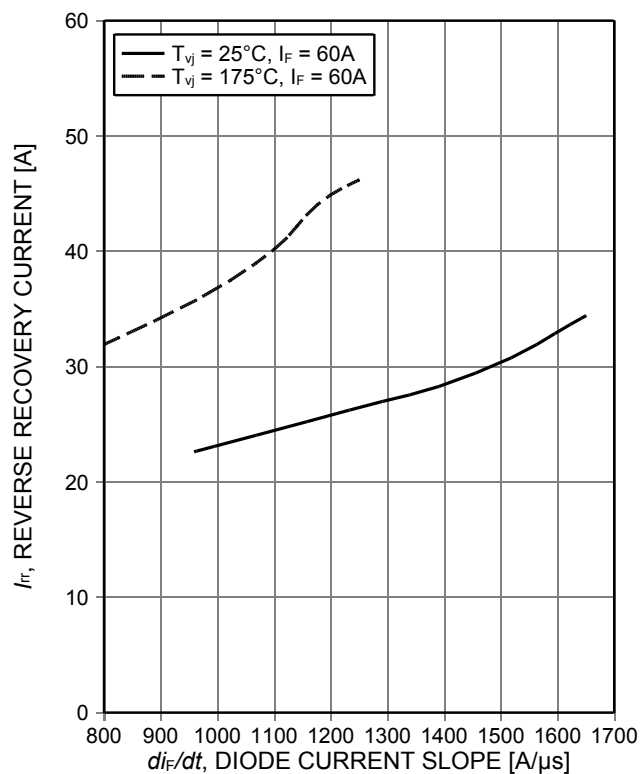


Figure 21. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

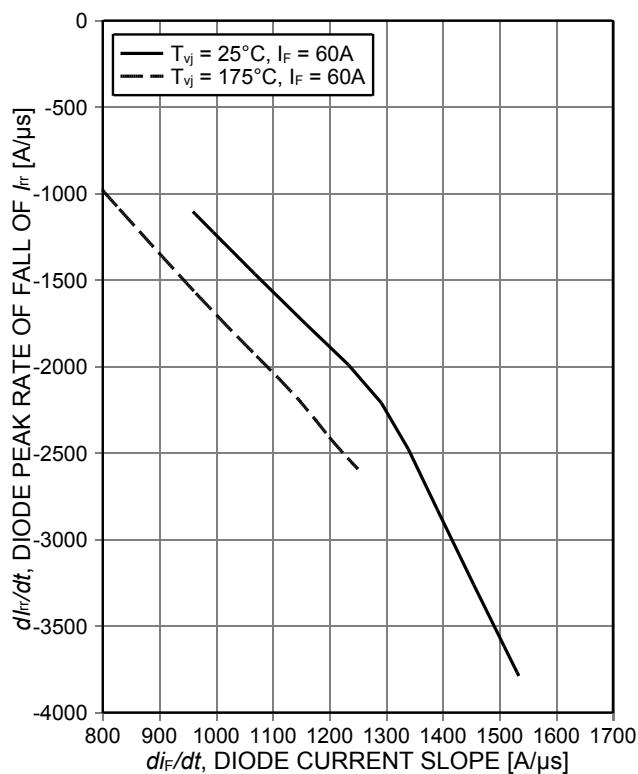


Figure 22. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=400V$)

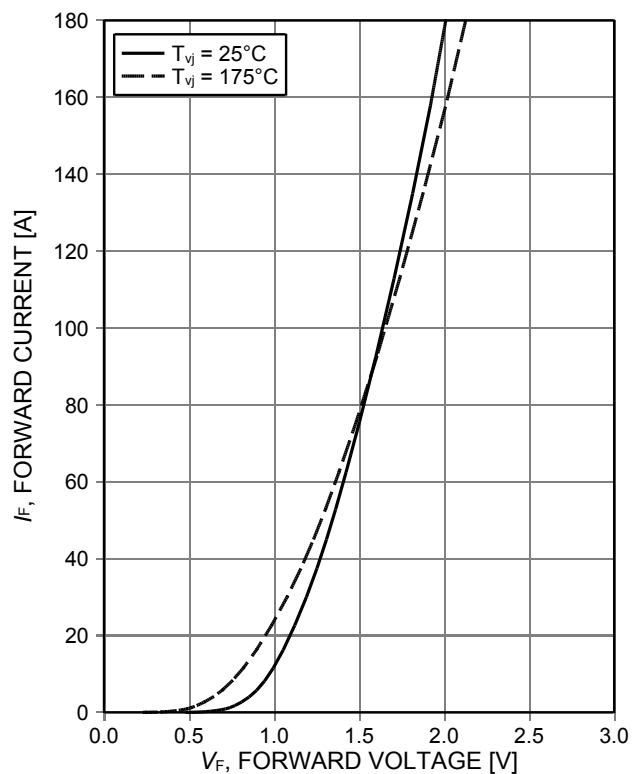


Figure 23. Typical diode forward current as a function of forward voltage

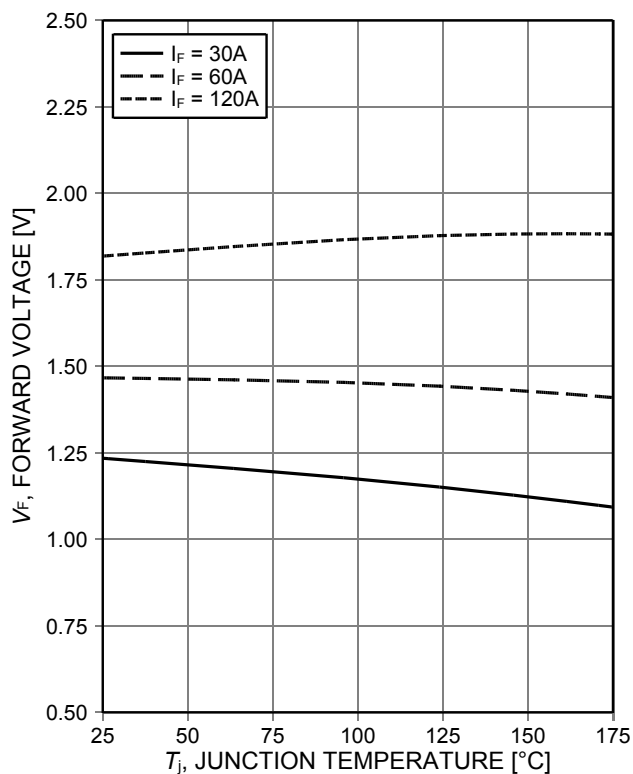
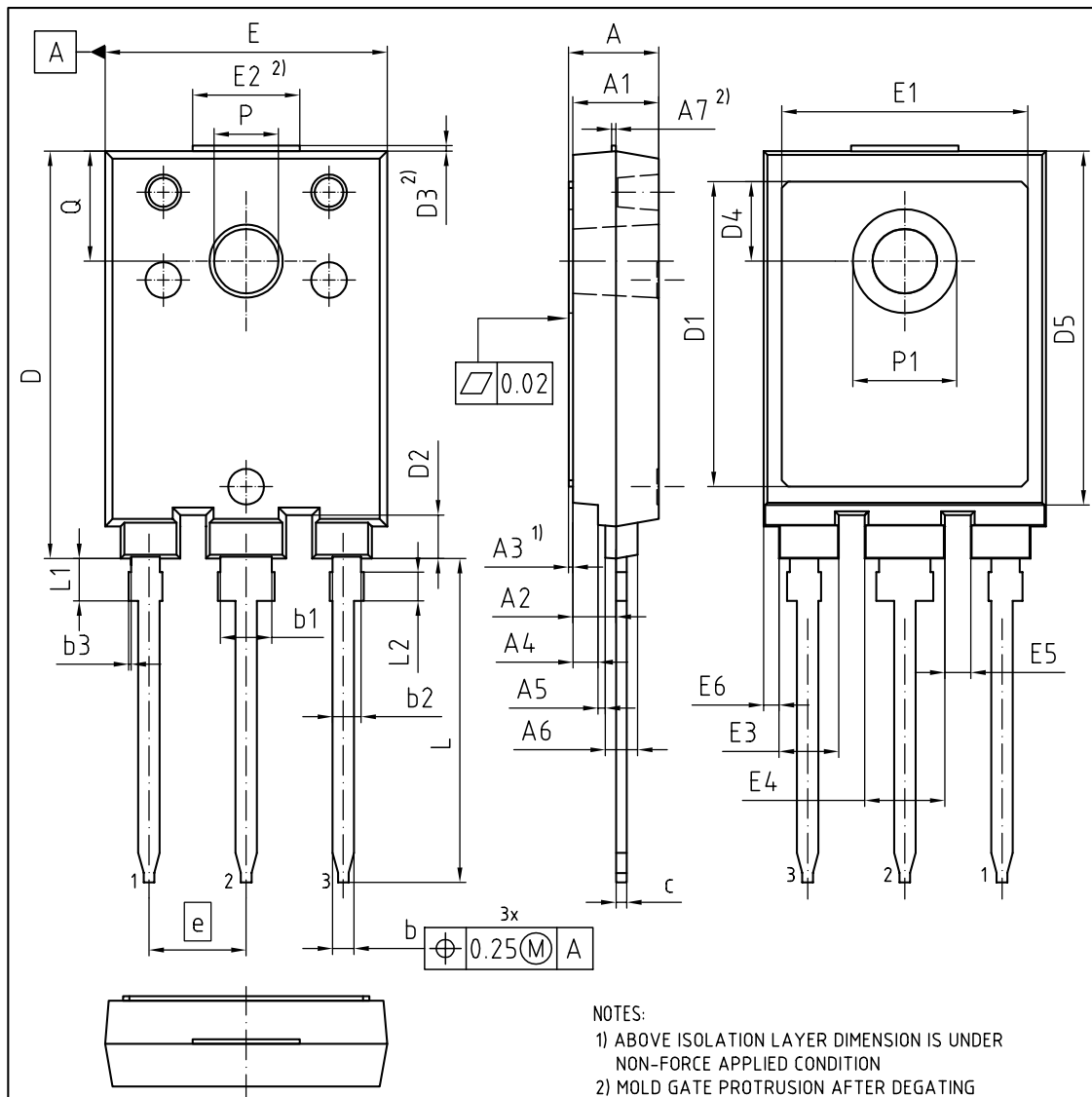


Figure 24. Typical diode forward voltage as a function of junction temperature

PG-HSIP247-3-2



NOTES:

- 1) ABOVE ISOLATION LAYER DIMENSION IS UNDER NON-FORCE APPLIED CONDITION
 2) MOLD GATE PROTRUSION AFTER DEGATING
 ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT

DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	-	5.18	e	5.44	
A1	4.70	4.90	E	15.70	15.90
A2	2.16	2.66	E1	13.68	13.88
A3	0.20	0.28	E2	(6.00)	
A4	1.30	1.50	E3	3.24	3.44
A5	0.31	0.51	E4	4.39	4.59
A6	1.70	1.90	E5	(1.45)	
A7	(0.25)		E6	0.76	0.96
b	1.10	1.30	L	18.01	18.21
b1	(2.88)		L1	2.26	2.46
b2	(1.60)		L2	1.50	1.70
b3	-	0.15	P	3.50	3.70
c	0.50	0.70	P1	5.70	5.90
D	22.70	22.90	Q	6.06	6.26
D1	16.96	17.16			
D2	2.34	2.54			
D3	-	0.30			
D4	4.35	4.55			
D5	19.70	19.90			

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REVISION 01
SCALE 3:1 0 1 2 3 4 5 6 7 8mm
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Testing Conditions

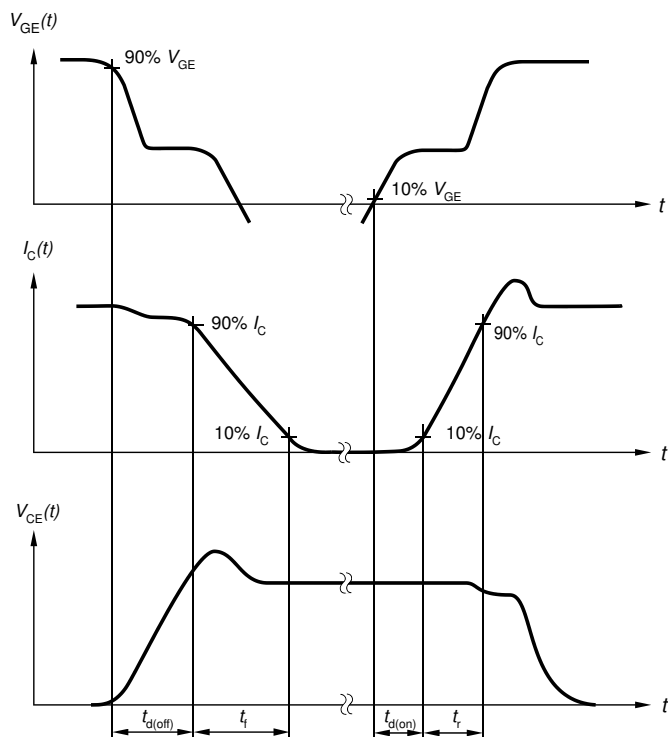


Figure A. Definition of switching times

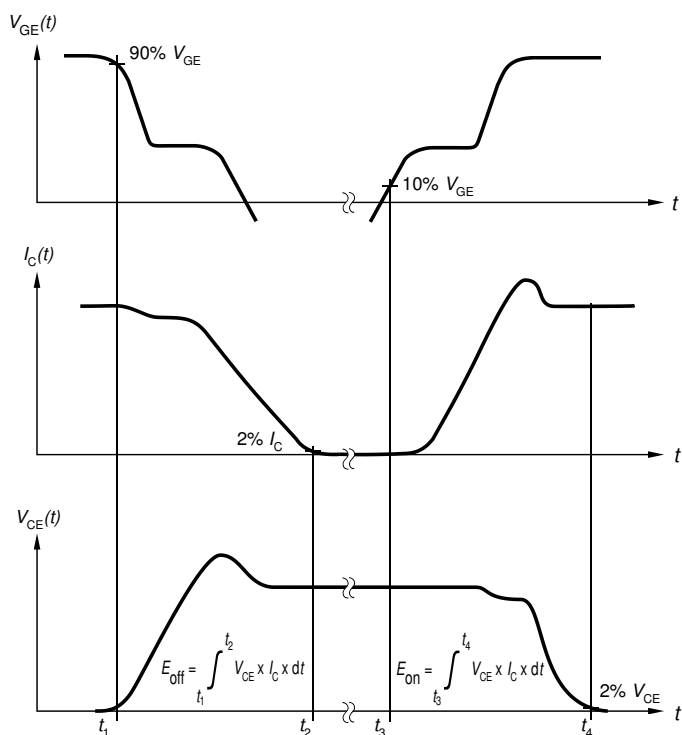


Figure B. Definition of switching losses

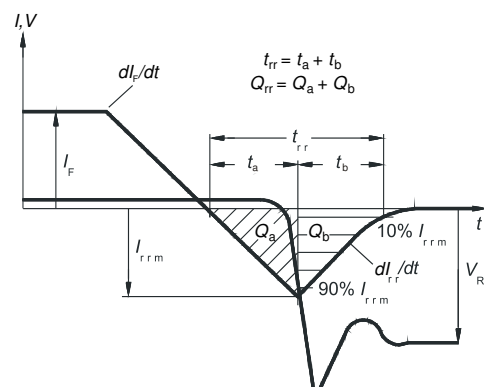


Figure C. Definition of diode switching characteristics

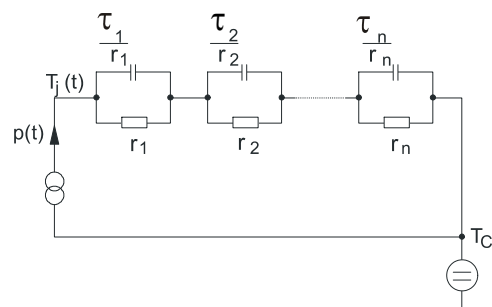


Figure D. Thermal equivalent circuit

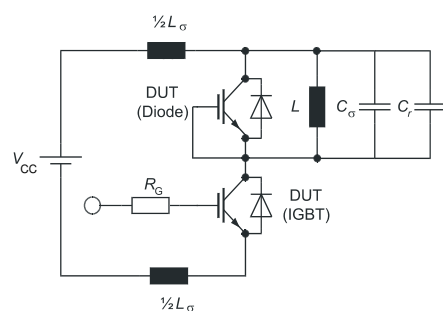


Figure E. **Dynamic test circuit**
 Parasitic inductance L_σ ,
 parasitic capacitor C_σ ,
 relief capacitor C_r ,
 (only for ZVT switching)

TRENCHSTOP™ 5 Advanced Isolation**Revision History**

IKFW75N65EH5**Revision: 2020-07-24, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2020-07-24	Final Data Sheet

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